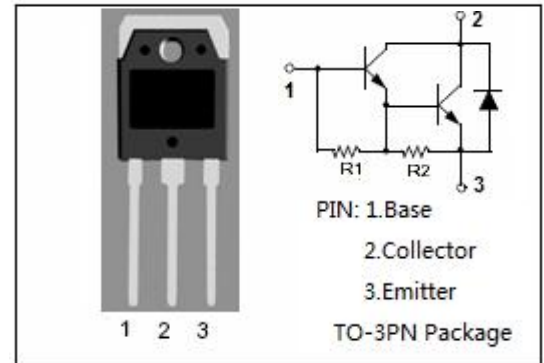


**isc Silicon NPN Darlington Power Transistor**
**BDV67D**
**DESCRIPTION**

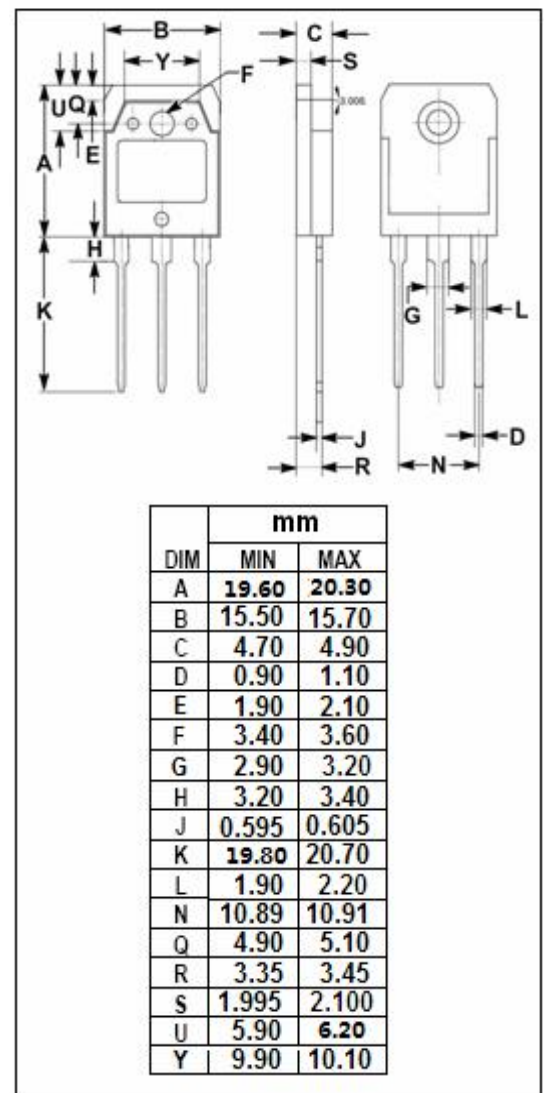
- Collector Current  $-I_C = 16A$
- Collector-Emitter Saturation Voltage-  
:  $V_{CE(sat)} = 2.0V(\text{Max.}) @ I_C = 10A$
- Complement to Type BDV66D
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Designed for audio output stages and general amplifier and switching applications


**ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	160	V
$V_{CEO}$	Collector-Emitter Voltage	150	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current-Continuous	16	A
$I_{CM}$	Collector Current-Peak	20	A
$I_B$	Base Current-Continuous	0.5	A
$P_C$	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	200	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-65~150	$^\circ\text{C}$


**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th-j-c}$	Thermal Resistance, Junction to Case	0.625	$^\circ\text{C/W}$

## isc Silicon NPN Darlington Power Transistor

## BDV67D

## ELECTRICAL CHARACTERISTICS

T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA ; I <sub>B</sub> = 0	150			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 40mA			2	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 10A ; V <sub>CE</sub> = 3V			2.5	V
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 1/2V <sub>CEOmax</sub> ; I <sub>B</sub> = 0			1	mA
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = V <sub>CB0max</sub> ; I <sub>E</sub> = 0			1	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			5	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 3 A ; V <sub>CE</sub> = 3V	1000			
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0 ; V <sub>CB</sub> = 10V; f <sub>test</sub> = 1MHz		300		pF
Switching times						
t <sub>on</sub>	Turn-on Time	I <sub>C</sub> = 10A; I <sub>B1</sub> = -I <sub>B2</sub> = 40mA; V <sub>CC</sub> = 12V		1		μ s
t <sub>off</sub>	Turn-off Time			3.5		μ s

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